

Attorney docket OKI 376

IN THE CLAIMS

1. (currently amended): A method of forming a dummy wafer comprising:
providing a dummy wafer having a front surface and a back surface;
forming a masking film ~~that covers a rear~~ on the back surface of ~~a silicon~~ the
dummy wafer;
spray coating aluminum on ~~[[a]] the~~ front surface of the ~~silicon~~ dummy wafer and thereby
forming so as to form an aluminum film;
spray coating a covering material on the aluminum film so that the aluminum film is
completely covered by ~~and thereby forming~~ a covering film; and
removing the masking film.
2. (currently amended): ~~[[A]]~~ The method of forming a dummy wafer as set forth in claim
1, ~~[[:]]~~ wherein the covering film is selected from the group consisting of a ceramic film and a
carbon film.
3. (currently amended): ~~[[A]]~~ The method of forming a dummy wafer as set forth in claim
2, ~~[[:]]~~ wherein ~~an end~~ a peripheral edge portion of the aluminum film is covered with ~~[[a]] the~~
ceramic film.
4. (currently amended): ~~[[A]]~~ The method of forming a dummy wafer as set forth in claim
2, ~~[[:]]~~ wherein the ceramic film is a film of aluminum oxide.
5. (currently amended): ~~[[A]]~~ The method of forming a dummy wafer as set forth in claim
2, ~~[[:]]~~ wherein the covering film has a film thickness distribution.

AMENDMENT

2

10/667,511

Attorney docket OKI 376

6. (currently amended): A method of forming a dummy wafer comprising:
processing aluminum into a wafer shape to provide an aluminum dummy wafer having a front surface and a back surface;
polishing ~~[[a]] the front~~ surface of ~~[[a]] the aluminum dummy~~ wafer; ~~that is made of~~ aluminum;
attaching an electrode to a part of the back surface of the aluminum dummy wafer;
covering the back surface with a masking film except the electrode;
applying anodic oxidation to the ~~surface of the~~ aluminum dummy wafer and thereby forming a film of so as to form an aluminum oxide film on the front surface of the aluminum dummy wafer; ~~[[and]]~~
removing the electrode and the masking film; and
applying mirror polishing to ~~a rear~~ the back surface of the wafer after the step of removing.

7.-8. (canceled)

9. (new): The method of forming a dummy wafer according to claim 6, wherein the aluminum dummy wafer has a thickness of about 1000 μm .

10. (new): The method of forming a dummy wafer according to claim 6, wherein the aluminum oxide film has a thickness of about 100 μm .

11. (new): The method of forming a dummy wafer according to claim 6, wherein the aluminum oxide film has a thickness of about less than 30 μm .

AMENDMENT

3

10/667,511

Attorney docket OKI 376

12. (new): The method of forming a dummy wafer according to claim 6, wherein the aluminum dummy wafer after applying mirror polishing has a thickness of about 670 μm .

13. (new): The method of forming a dummy wafer according to claim 6, further comprises washing the aluminum dummy wafer with deionized water after applying the mirror polishing.

14. (new): A method of forming a dummy wafer comprising:
providing a silicon dummy wafer having a front surface and a back surface;
forming a masking film on the back surface of the silicon dummy wafer;
thermally spraying aluminum on the front surface of the silicon dummy wafer so as to form an aluminum film on the front surface of the silicon dummy wafer;
thermally spraying a covering material on the aluminum film so that the aluminum film is covered by a covering film;
removing the masking film after thermally spraying the covering material; and
washing the silicon dummy wafer with deionized water after removing the masking film.

15. (new): The method of forming a dummy wafer according to claim 14, wherein blasting is not applied to the front surface of the silicon dummy wafer.

16. (new): The method of forming a dummy wafer according to claim 14, wherein the covering material is selected from the group consisting of ceramic and carbon.

17. (new): The method of forming a dummy wafer according to claim 16, wherein the ceramic is made of aluminum oxide.

AMENDMENT

4

10/667,511

Attorney docket OKI 376

18. (new): The method of forming a dummy wafer according to claim 14, wherein a thickness of a peripheral portion of the aluminum film and the covering film is smaller than that of a central portion.

19. (new): The method of forming a dummy wafer according to claim 18, wherein the thickness of the peripheral portion is about 670 μm .

AMENDMENT

5

10/667,511